Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT54 (TO-92) plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- · 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- · High immunity to false turn-on by dV/dt
- High voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

3. Applications

- · General purpose motor control
- Small loads in washing machines
- Solenoid drivers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 54$ °C; $\overline{Fig. 1}$; $\overline{Fig. 2}$; $\overline{Fig. 3}$	-	-	1	Α
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	1	-	10	mA

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2——T1
2	G	gate		G sym051
3	T1	main terminal 1	TO-92 (SOT54)	Symocr

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA201-800E	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 54$ °C; Fig. 1; Fig. 2; Fig. 3	-	1	Α
I _{TSM}	non-repetitive peak on-	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.8 \text{ms}$	-	13.7	Α
	state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	12.5	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I_{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
Tj	junction temperature		-40	125	°C

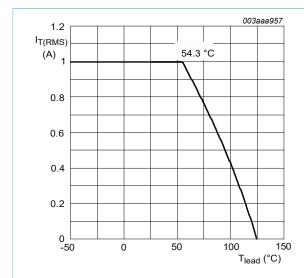


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

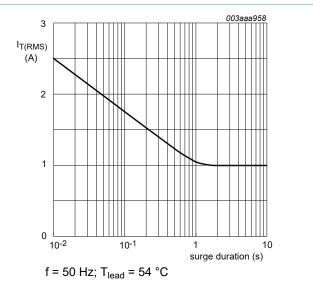


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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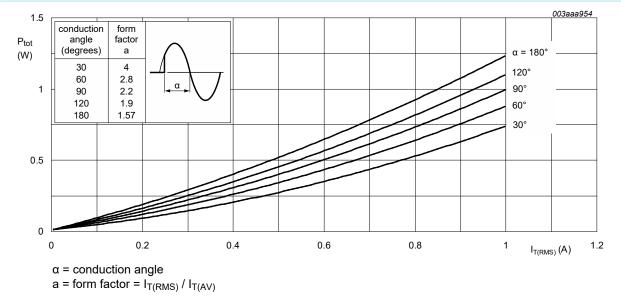


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

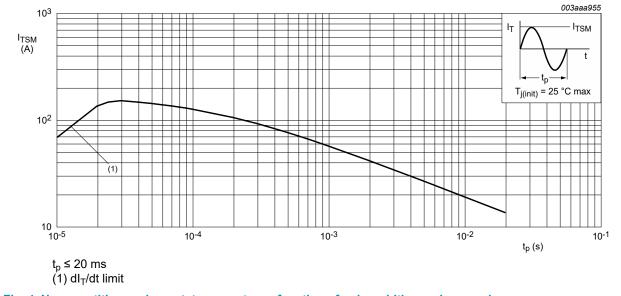


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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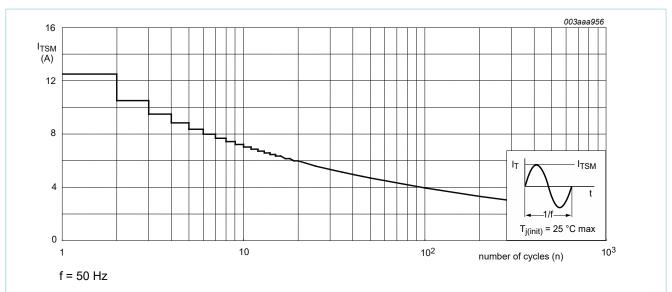


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

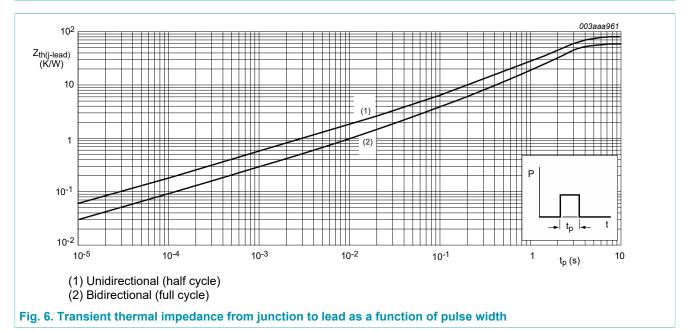
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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	_	60	K/W
		half cycle; Fig. 6	-	_	80	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	1	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	1	-	10	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	12	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	12	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	12	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V_{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.2	0.7	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics		,			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/s; (snubberless condition); gate open circuit	2.5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 1 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; gate open circuit}$	3.5	-	-	A/ms

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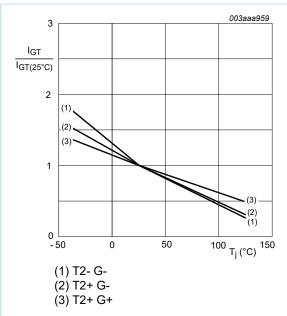


Fig. 7. Normalized gate trigger current as a function of junction temperature

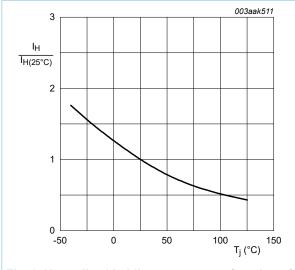


Fig. 9. Normalized holding current as a function of junction temperature

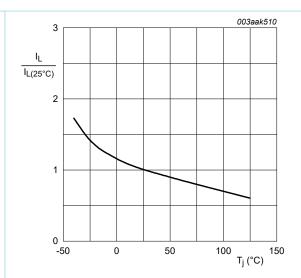
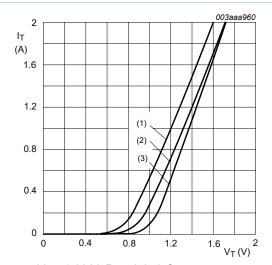


Fig. 8. Normalized latching current as a function of junction temperature



 $\begin{array}{l} \text{V}_{\text{o}} = 1.02 \text{ V}; \text{ R}_{\text{s}} = 0.358 \ \Omega \\ \text{(1)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ typical values} \\ \text{(2)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ maximum values} \\ \text{(3)} \text{ T}_{\text{j}} = 25 \ ^{\circ}\text{C}; \text{ maximum values} \end{array}$

Fig. 10. On-state current as a function of on-state voltage

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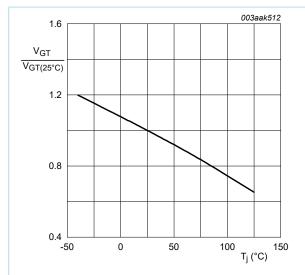


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

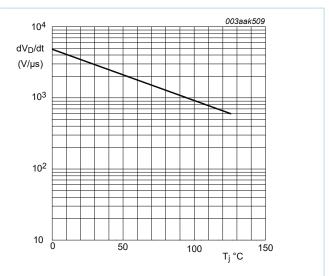
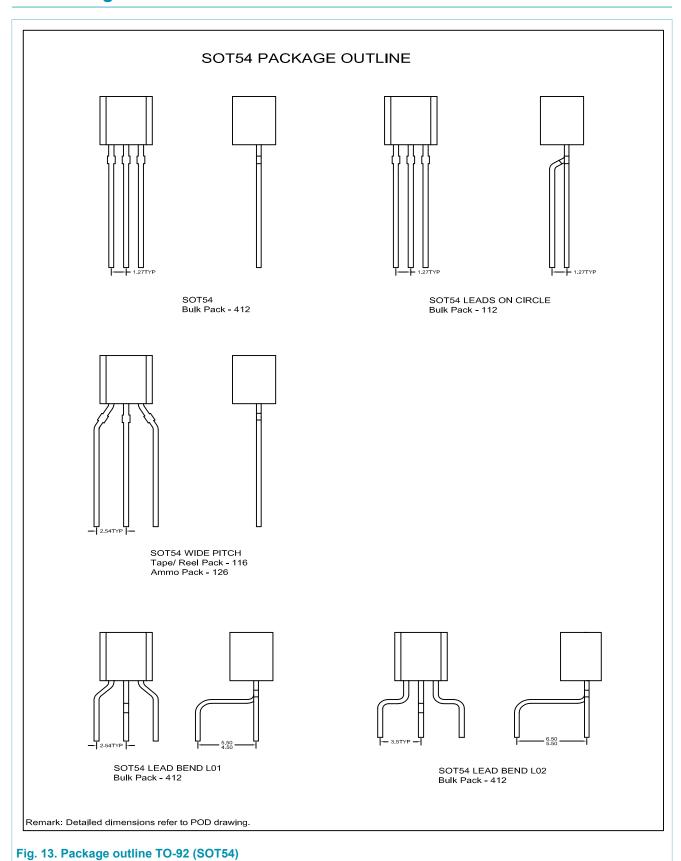


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

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10. Package outline



BTA201-800E

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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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